

isc Silicon NPN Power Transistor

2SC3412

DESCRIPTION

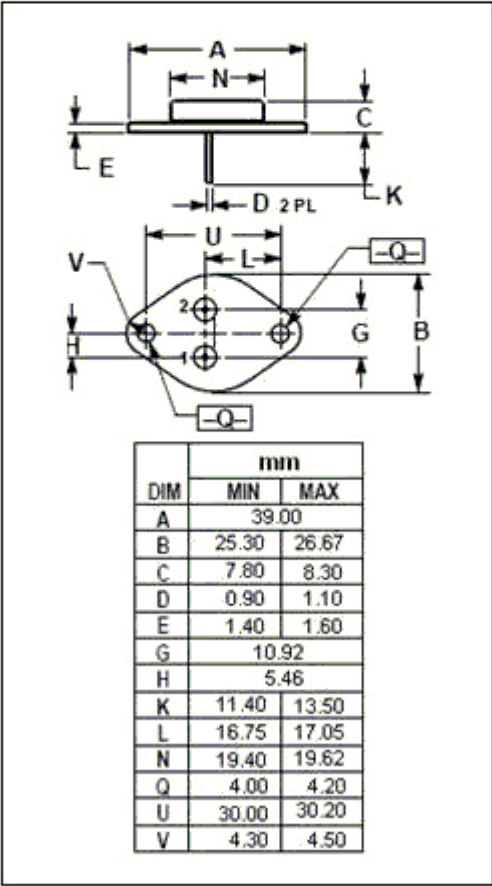
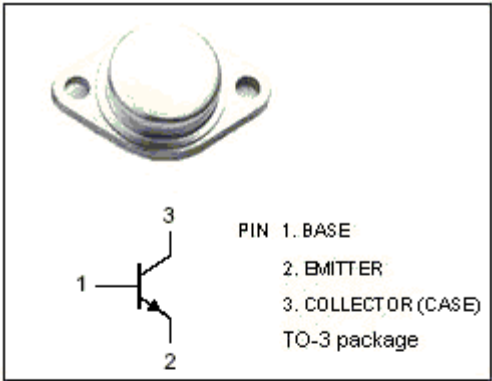
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO}= 500V$ (Min)
- High Power Dissipation

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	1300	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SC3412****ELECTRICAL CHARACTERISTICS****T_C=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	500			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1300V; R _{BE} = 0			0.5	mA

Switching Times

t _{stg}	Storage Time	I _C = 5A; I _{B1} = 1A		3		μ s
t _f	Fall Time			0.2		μ s